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April 1999

# FDN335N

### 

### FDN335N N-Channel 2.5V Specified PowerTrench<sup>™</sup> MOSFET

### **General Description**

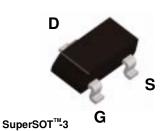
This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

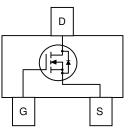
### Applications

- DC/DC converter
- Load switch

### Features

- 1.7 A, 20 V.  $R_{DS(ON)} = 0.07 \ \Omega \ @ V_{GS} = 4.5 \ V$  $R_{DS(ON)} = 0.100 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Low gate charge (3.5nC typical).
- High performance trench technology for extremely low  $\rm R_{\rm DS(ON)}.$
- High power and current handling capability.





	•	Inless otherwise noted		
Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		20	V
V <sub>GSS</sub>	Gate-Source Voltage	<u>+</u> 8	V	
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	1.7	А
	- Pulsed		8	
PD	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T <sub>J</sub> , T <sub>stq</sub>	Operating and Storage Junction Tempera	ature Range	-55 to +150	۰C
<u>Therma</u> <sub>Rөл</sub>	I Characteristics Thermal Resistance, Junction-to-Ambient	t (Note 1a)	250	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	istance, Junction-to-Case (Note 1) 75		°C/W
Packag	e Outlines and Ordering In			0
Device	e Marking Device	Reel Size	Tape Width	Quantity
	335 FDN335N	7"	8mm	3000 units

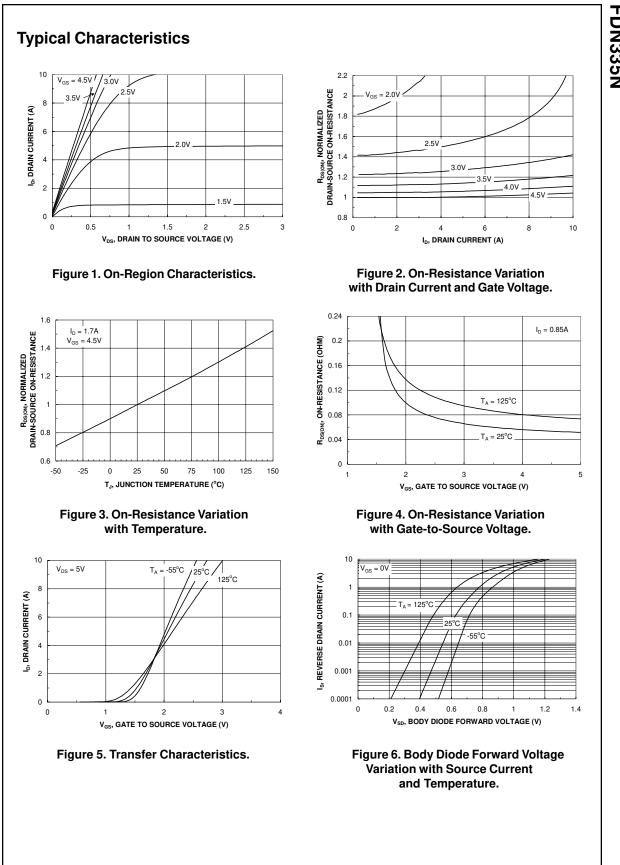
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \ \mu\text{A}$	20			V
$\Delta BV_{DSS}$ $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A,Referenced to 25°C		14		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 16 V, V_{GS} = 0 V$			1	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -8 \ V, \ V_{DS} = 0 \ V$			-100	nA
On Chara	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.4	0.9	1.5	V
$\frac{\Delta VGS(th)}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A,Referenced to 25°C		-3		mV/∘C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$ \begin{array}{l} V_{GS} = 4.5 \ V, \ I_D = 1.7 \ A \\ V_{GS} = 4.5 \ V, \ I_D = 1.7 \ A, \\ T_J = 125^{\circ}C \\ V_{GS} = 2.5 \ V, \ I_D = 1.5 \ A \end{array} $		0.055 0.079 0.078	0.070 0.120 0.100	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	8			Α
<b>g</b> fs	Forward Transconductance	$V_{DS} = 5 V, I_D = 1.5 A$		7		S
C <sub>iss</sub>	Characteristics	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		310		рF
Coss	Output Capacitance	-		80		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			40		pF
<u>Switchin</u>	g Characteristics (Note 2)	1	·	i	ï	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ A},$		5	15	ns
tr	Turn-On Rise Time	$V_{GS}$ = 4.5 V, $R_{GEN}$ = 6 $\Omega$		8.5	17	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			11	20	ns
t <sub>f</sub>	Turn-Off Fall Time			3	10	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.7 \text{ A},$		3.5	5	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 4.5 V,$		0.55		nC
Q <sub>gd</sub>	Gate-Drain Charge			0.95		nC
Drain-So	urce Diode Characteristics a	and Maximum Ratings				
ls	Maximum Continuous Drain-Source	Diode Forward Current			0.42	А
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \ V, \ I_S = 0.42 \ A$ (Note 2)		0.7	1.2	V
	sum of the junction-to-case and case-to-ambient rain pins. $R_{_{BCA}}$ is guaranteed by design while $R_{_{BCA}}$ is a		erence is o	defined as t	he solder m	ounting

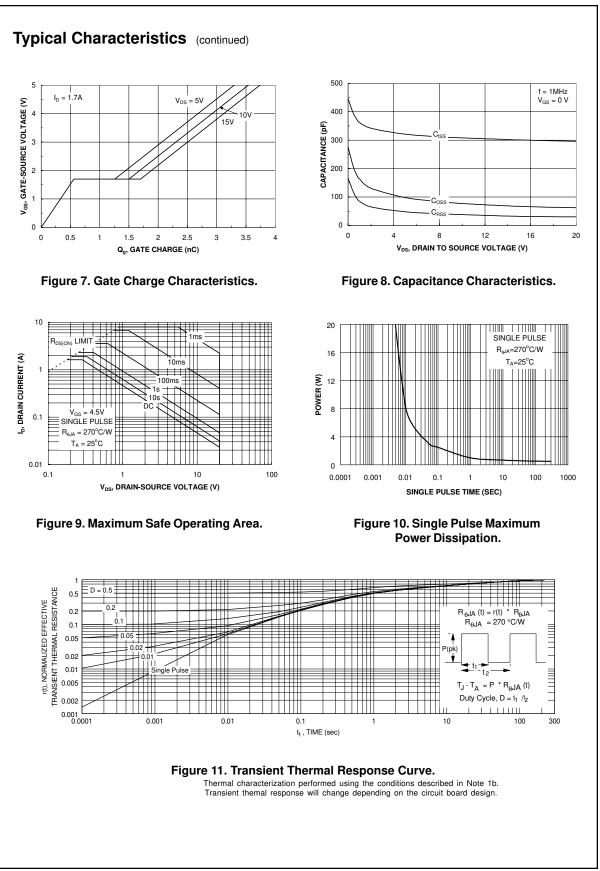
mounted on a 0.02 in<sup>2</sup> Pad of 2 oz. Cu. Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty}~\text{Cycle} \leq 2.0\%$ 

FDN335N



# FDN335N



FDN335N Rev. C

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